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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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# HiPerFAST™ IGBT ISOPLUS247™

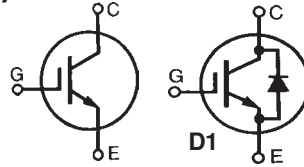
IXGR 40N60B2  
IXGR 40N60B2D1

$V_{CES} = 600\text{ V}$   
 $I_{C25} = 75\text{ A}$   
 $V_{CE(sat)} = 1.9\text{ V}$   
 $t_{fi\text{typ}} = 82\text{ ns}$

## C2-Class High Speed IGBTs (Electrically Isolated Back Surface)

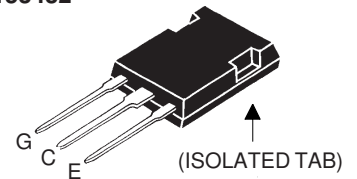
Optimized for 10-25 KHz hard switching  
and up to 150 KHz resonant switching

Preliminary Data Sheet



Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	600	V
$V_{CGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GE} = 1\text{ M}\Omega$	600	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$	60	A
$I_{C110}$	$T_C = 110^\circ\text{C}$	33	A
$I_{F110}$	$T_C = 110^\circ\text{C}$ (IXGR40N60B2D1)	25	A
$I_{CM}$	$T_C = 25^\circ\text{C}$ , 1 ms	200	A
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15\text{ V}$ , $T_{VJ} = 125^\circ\text{C}$ , $R_G = 10\ \Omega$ Clamped inductive load @ $\leq 600\text{ V}$	$I_{CM} = 80$	A
$P_C$	$T_C = 25^\circ\text{C}$	167	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$V_{ISOL}$	50/60 Hz RMS, $t = 1\text{ m}$	2500	V
	Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
<b>Weight</b>		6	g

ISOPLUS247 (IXGR)  
E153432



G = Gate,  
E = Emitter

C = Collector,

### Features

- DCB Isolated mounting tab
- Meets TO-247AD package Outline
- High current handling capability
- Latest generation HDMOS™ process
- MOS Gate turn-on - drive simplicity

### Applications

- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

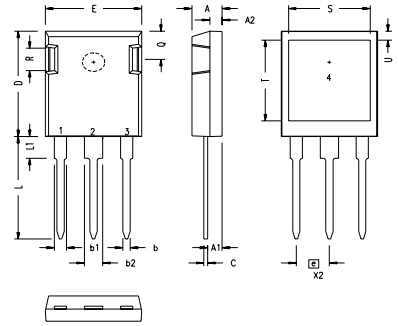
### Advantages

- Easy assembly
- High power density
- Very fast switching speeds for high frequency applications

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{GE(th)}$	$I_C = 250\ \mu\text{A}$ , $V_{CE} = V_{GE}$	3.0		5.0 V
$I_{CES}$	$V_{CE} = V_{CES}$ $V_{GE} = 0\text{ V}$			50 $\mu\text{A}$ 1 mA
$I_{GES}$	$V_{CE} = 0\text{ V}$ , $V_{GE} = \pm 20\text{ V}$			$\pm 100\text{ nA}$
$V_{CE(sat)}$	$I_C = 30\text{ A}$ , $V_{GE} = 15\text{ V}$			1.9 V

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)			
		min.	typ.	max.	
$g_{fs}$	$I_C = 30\text{ A}; V_{CE} = 10\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $\leq 2\%$	20	36	S	
$C_{ies}$ $C_{oes}$ $C_{res}$	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		2560	pF	
			210	pF	
			54	pF	
$Q_g$ $Q_{ge}$ $Q_{gc}$	$I_C = 30\text{ A}, V_{GE} = 15\text{ V}, V_{CE} = 300\text{ V}$		100	nC	
			15	nC	
			36	nC	
$t_{d(on)}$ $t_{ri}$ $t_{d(off)}$ $t_{fi}$ $E_{off}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 30\text{ A}, V_{GE} = 15\text{ V}$ $V_{CE} = 400\text{ V}, R_G = 3.3\ \Omega$		18	ns	
			20	ns	
			130	200	ns
			82	150	ns
			0.4	0.8	mJ
$t_{d(on)}$ $t_{ri}$ $E_{on}$ $t_{d(off)}$ $t_{fi}$ $E_{off}$	<b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = 30\text{ A}, V_{GE} = 15\text{ V}$ $V_{CE} = 400\text{ V}, R_G = 3.3\ \Omega$		18	ns	
			20	ns	
			0.3	mJ	
			240	ns	
			150	ns	
			1.10	mJ	
$R_{thJC}$ $R_{thCK}$			0.75	K/W	
		0.15		K/W	

**ISOPLUS 247 Outline**



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b1	.075	.084	1.91	2.13
b2	.115	.123	2.92	3.12
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
E	.620	.635	15.75	16.13
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.520	.540	13.21	13.72
T	.620	.640	15.75	16.26
U	.065	.080	1.65	2.03

- 1 - GATE
- 2 - DRAIN (COLLECTOR)
- 3 - SOURCE (EMITTER)
- 4 - NO CONNECTION

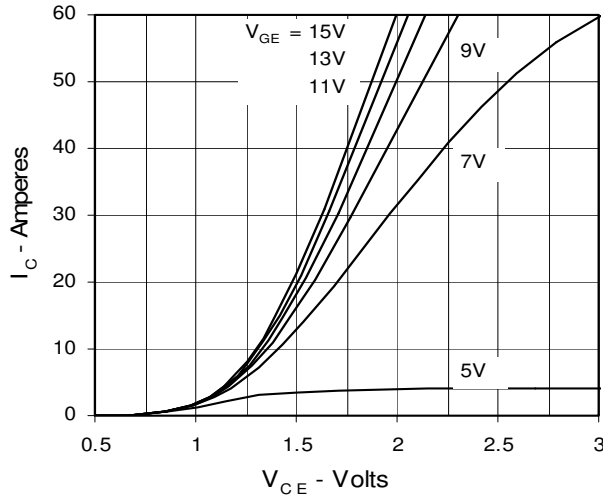
NOTE: This drawing will meet all dimensions requirement of JEDEC outline TO-247AD except screw hole.

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_F$	$I_F = 30\text{ A}, V_{GE} = 0\text{ V}$ , Pulse test $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.6 V 2.5 V
$I_{RM}$ $t_{rr}$	$I_F = 30\text{ A}, V_{GE} = 0\text{ V}, -di_F/dt = 100\text{ A}/\mu\text{s}, T_J = 100^\circ\text{C}$ $V_R = 100\text{ V}, T_J = 100^\circ\text{C}$ $I_F = 1\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}; V_R = 30\text{ V}$		100	4 A ns
			25	ns
$R_{thJC}$		0.9	1.1	K/W

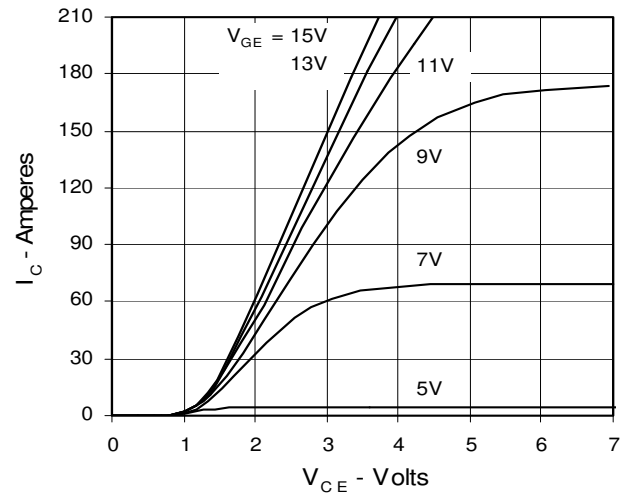
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065B1	6,683,344	6,727,585
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123B1	6,534,343	6,710,405B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	

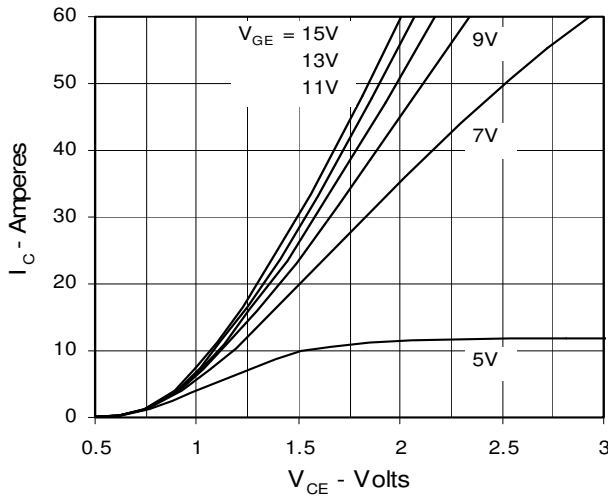
**Fig. 1. Output Characteristics  
@ 25 Deg. C**



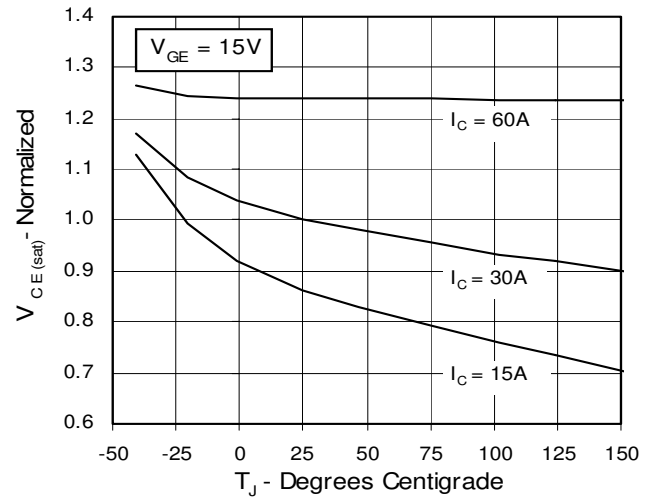
**Fig. 2. Extended Output Characteristics  
@ 25 deg. C**



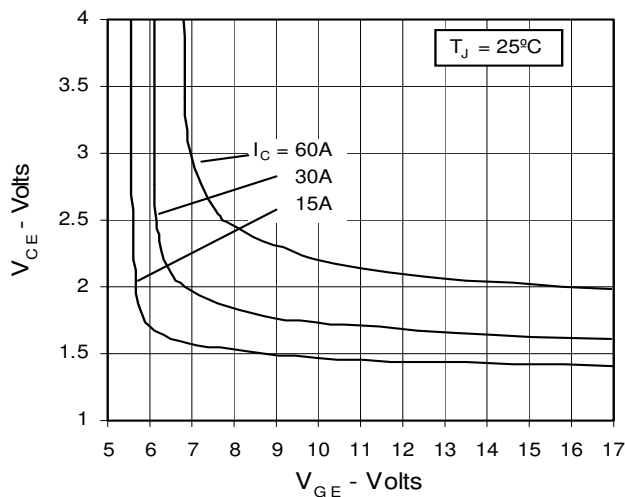
**Fig. 3. Output Characteristics  
@ 125 Deg. C**



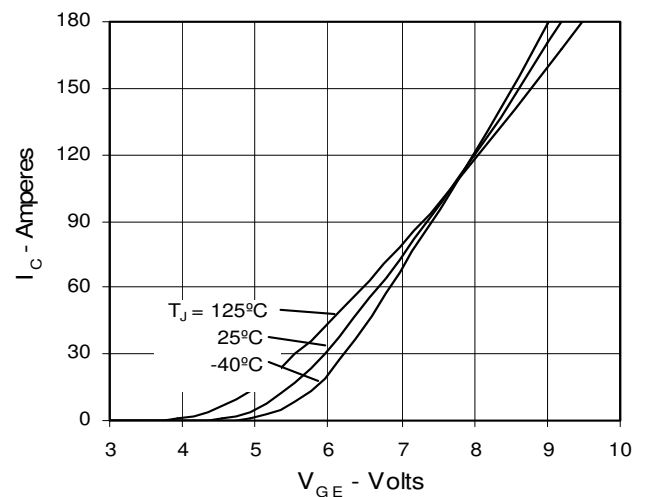
**Fig. 4. Dependence of  $V_{CE(sat)}$  on Temperature**



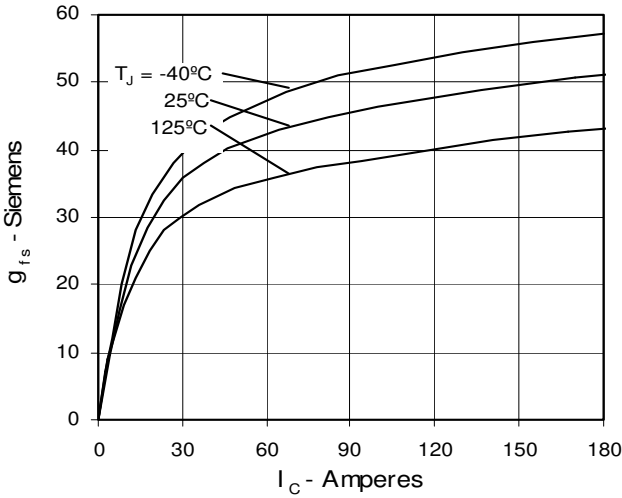
**Fig. 5. Collector-to-Emitter Voltage  
vs. Gate-to-Emitter voltage**



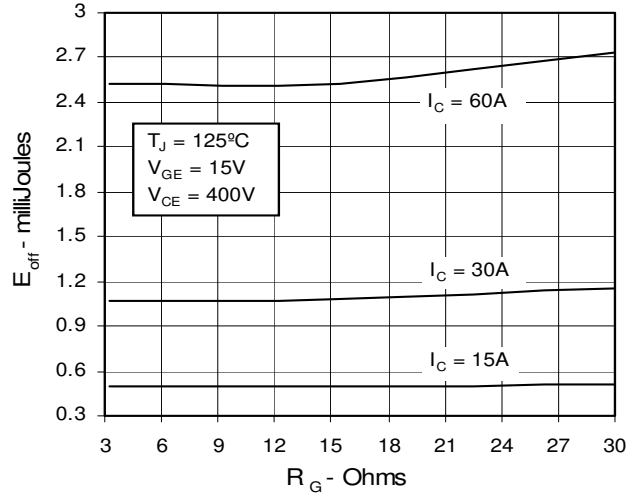
**Fig. 6. Input Admittance**



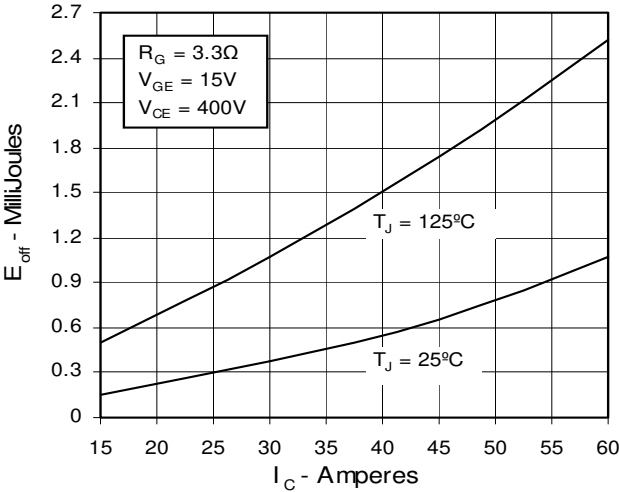
**Fig. 7. Transconductance**



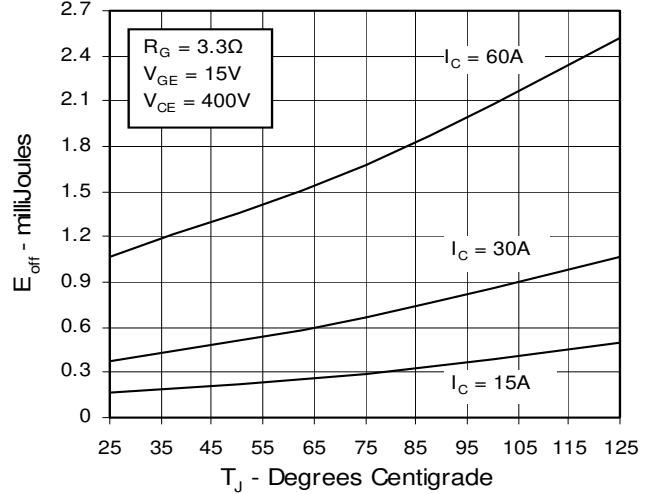
**Fig. 8. Dependence of Turn-Off Energy on  $R_G$**



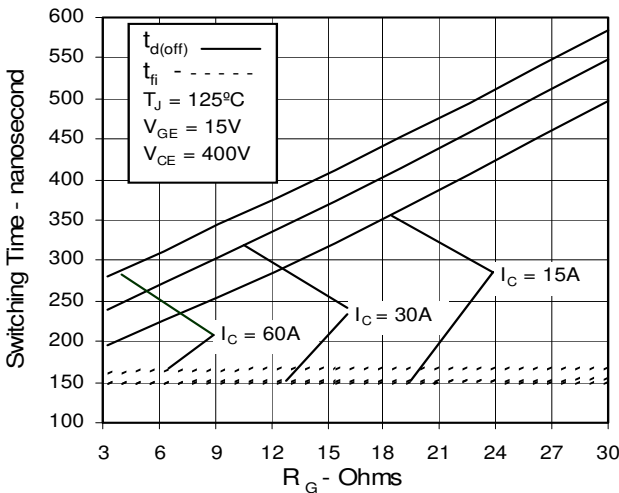
**Fig. 9. Dependence of Turn-Off Energy on  $I_C$**



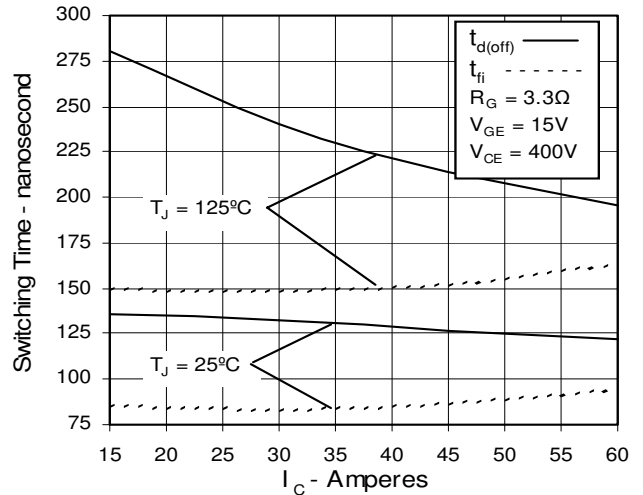
**Fig. 10. Dependence of Turn-Off Energy on Temperature**



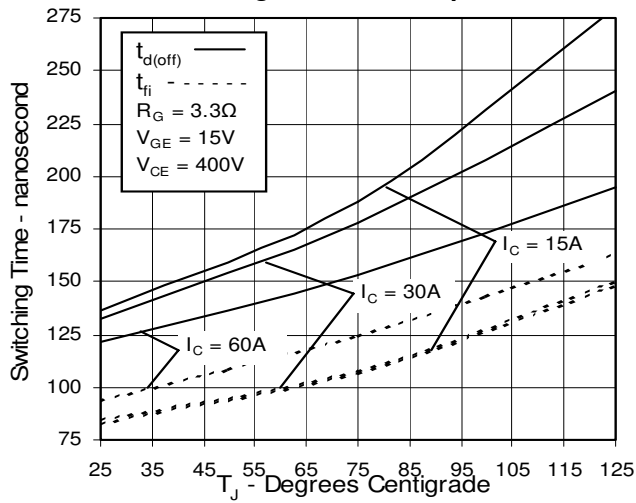
**Fig. 11. Dependence of Turn-Off Switching Time on  $R_G$**



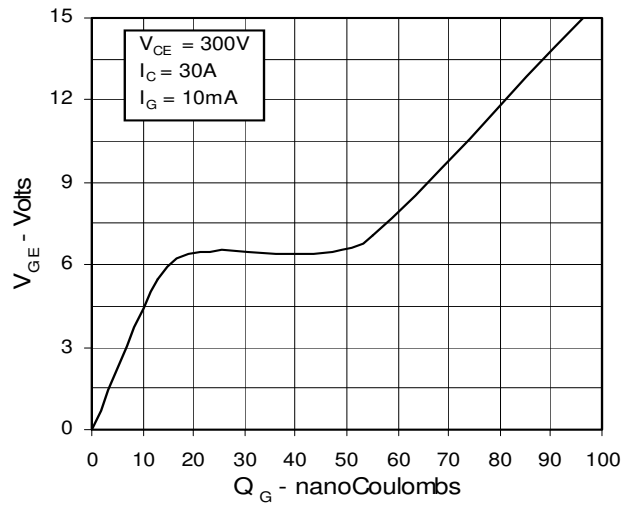
**Fig. 12. Dependence of Turn-Off Switching Time on  $I_C$**



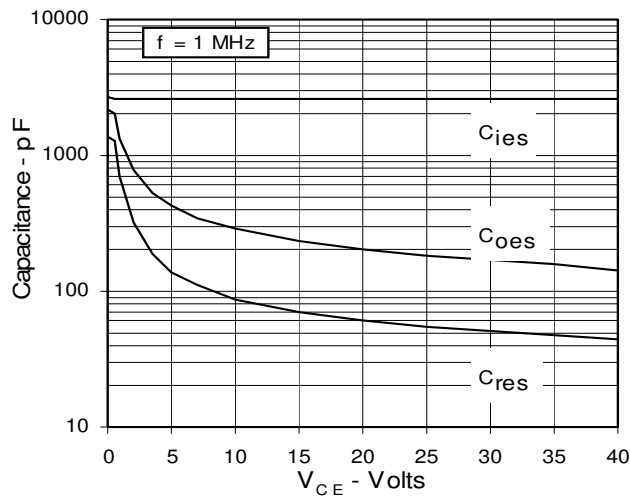
**Fig. 13. Dependence of Turn-Off Switching Time on Temperature**



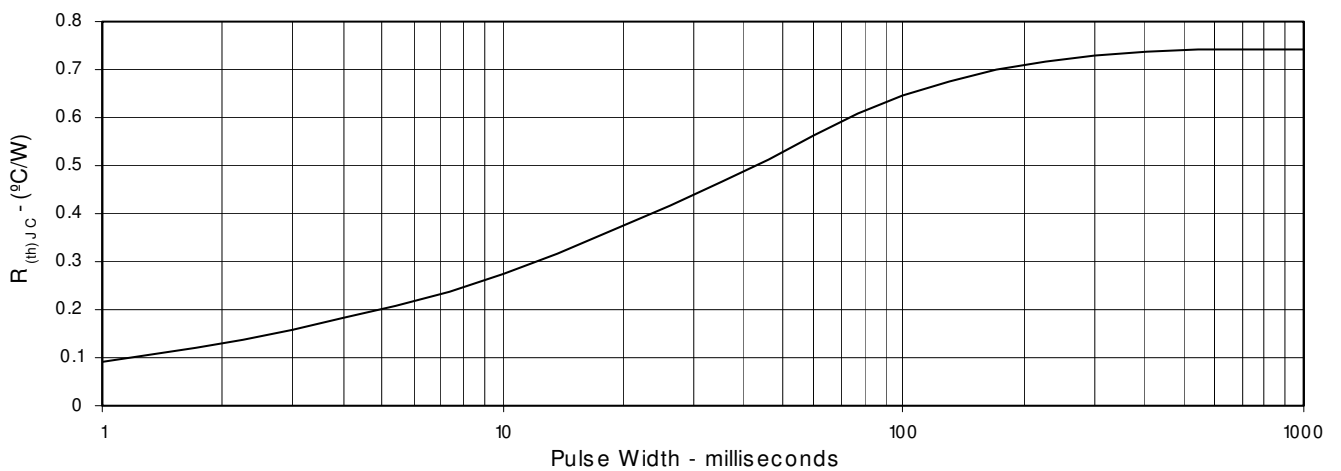
**Fig. 14. Gate Charge**



**Fig. 15. Capacitance**



**Fig. 13. Maximum Transient Thermal Resistance**



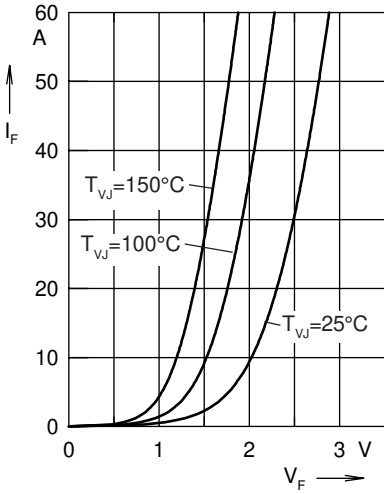


Fig. 17 Forward current  $I_F$  versus  $V_F$

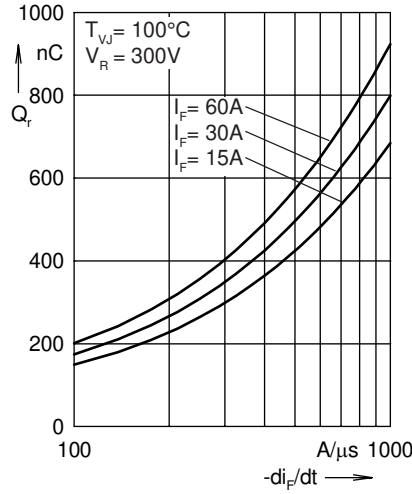


Fig. 18 Reverse recovery charge  $Q_r$  versus  $-di_F/dt$

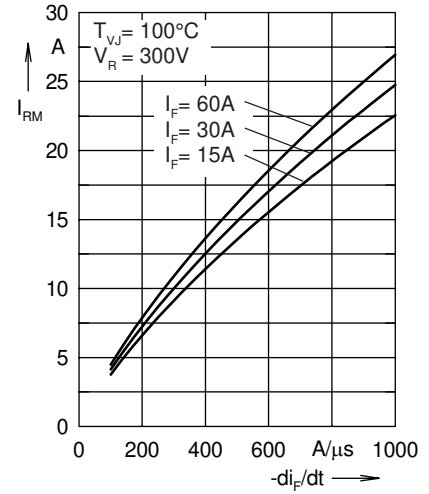


Fig. 19 Peak reverse current  $I_{RM}$  versus  $-di_F/dt$

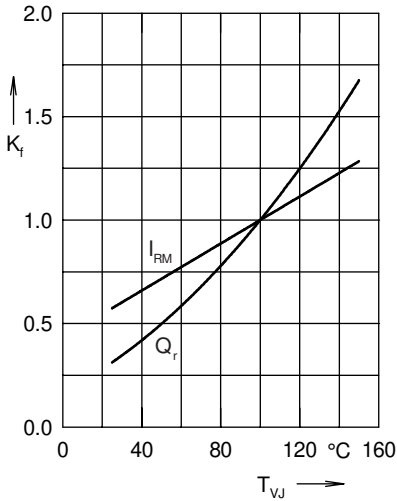


Fig. 20 Dynamic parameters  $Q_r$ ,  $I_{RM}$  versus  $T_{VJ}$

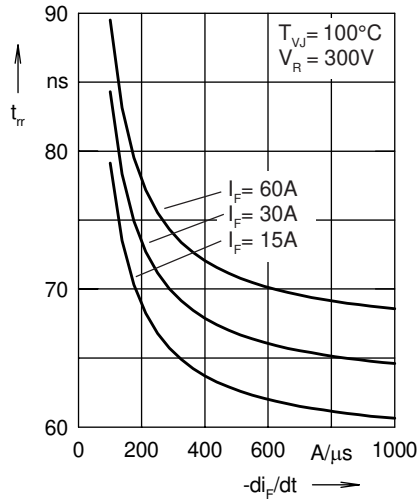


Fig. 21 Recovery time  $t_{tr}$  versus  $-di_F/dt$

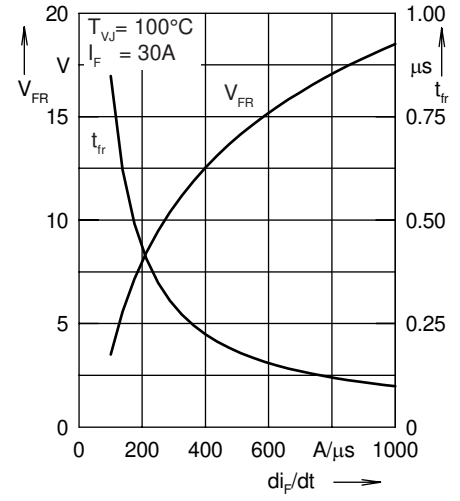


Fig. 22 Peak forward voltage  $V_{FR}$  and  $t_{tr}$  versus  $di_F/dt$

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.436	0.0055
2	0.482	0.0092
3	0.117	0.0007
4	0.115	0.0418

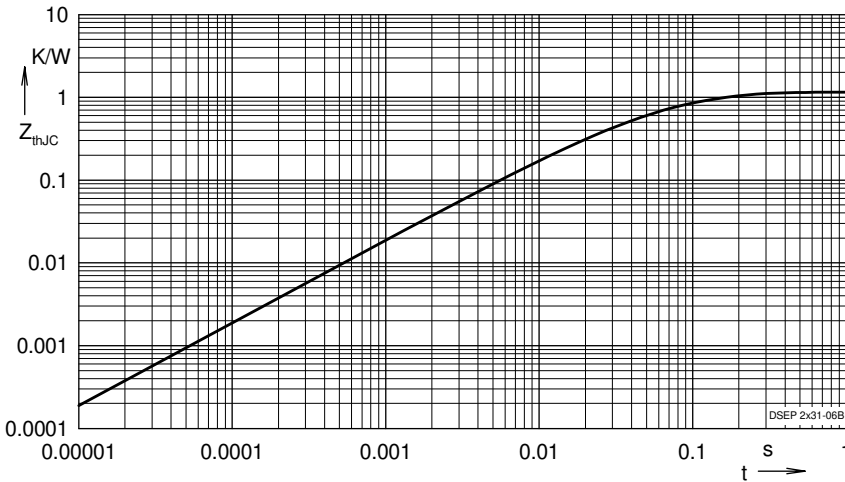


Fig. 23 Transient thermal resistance junction to case